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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







FC4B22180L1

Panasonic

FC4B22180L1

Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

■ Features

- Low source-source ON resistance:Rss(on) typ. = $10 \text{ m}\Omega(VGS = 3.8 \text{ V})$
- CSP(Chip Size Package)
- RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: 17

■ Packaging

Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter		Symbol	Rating	Unit	
Source-source Voltage		VSS	20	V	
Gate-source Voltage		VGS	±8	V	
Source Current	DC *1	IS1	5	Α	
	DC *2	IS2	10	Α	
	Pulse *3	ISp	50	Α	
Total Power Dissipation	DC *1	PD1	0.4	W	
Total Fower Dissipation	DC *2	PD2	1.5	W	
Channel Temperature		Tch	150	°C	
Storage Temperature Range		Tstg	-55 to +150	°C	
Thermal Resistance (ch-a)	DC *1	Rth1	312	°C/W	
	DC *2	Rth2	83	°C/W	

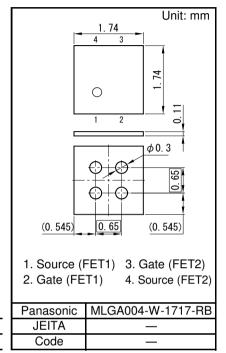
Note *1 Mounted on FR4 board

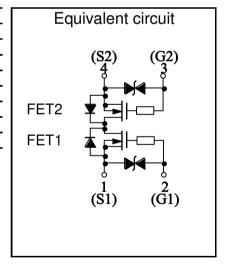
Established: 2015-10-23

Revised

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- (25.4mm \times 25.4mm \times t1.0mm, 36 μ m Copper)
- *2 Mounted on Ceramic substrate $(70 \text{ mm} \times 70 \text{ mm} \times t1.0 \text{ mm}).$
- *3 $t = 10 \mu s$, Duty Cycle $\leq 1 \%$





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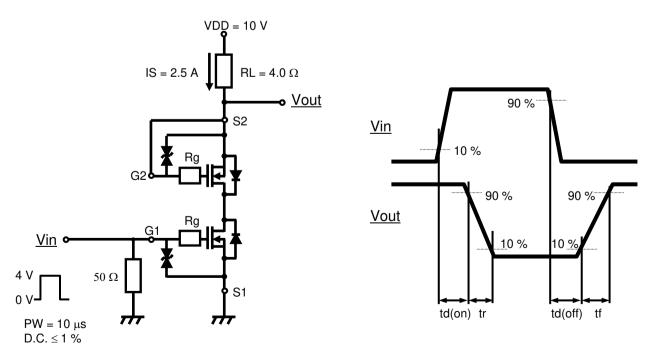
■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	20			V	
Zero Gate Voltage Source Current	ISSS	VSS = 20 V, VGS = 0 V			1.0	μΑ	
Gate-source Leakage Current	IGSS	$VGS = \pm 8 \text{ V}, VSS = 0 \text{ V}$			±10	μА	
		$VGS = \pm 5 V$, $VSS = 0 V$			±1.0	μΑ	
Gate-source Threshold Voltage	Vth	IS = 0.64 mA, VSS = 10 V	0.35	0.90	1.4	V	
Source-source On-state Resistance	RSS(on)1	IS = 2.5 A, VGS = 4.5 V	7	9.4	11.9		
	RSS(on)2	IS = 2.5 A, VGS = 3.8 V	7.3	10	12.9	mΩ	
	RSS(on)3	IS = 2.5 A, VGS = 3.1 V	8.1	11.1	15.8		
	RSS(on)4	IS = 2.5 A, VGS = 2.5 V	8.6	13.4	22.6		
Body Diode Forward Voltage	VF(s-s)	IF = 2.5 A, VGS = 0 V		0.8	1.2	V	
Input Capacitance *1	Ciss			2440		pF	
Output Capacitance *1	Coss	VSS = 10 V, VGS = 0 V, f = 1 MHz		200			
Reverse Transfer Capacitance *1	Crss			160			
Turn-on delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		0.9			
Rise Time *1,*2	tr	IS = 2.5 A		1.6		μS	
Turn-off delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V		5		μS	
Fall Time *1,*2	tf	IS = 2.5 A		2.4			
Total Gate Charge *1	Qg	VDD = 10 V		23			
Gate-source Charge *1	Qgs	VGS = 0 to 4.0 V,		6		nC	
Gate-drain Charge *1	Qgd	IS = 2.5 A		5			

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

- *1 Guaranteed by design, not subject to production testing
- *2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

Note2: Measurement circuit

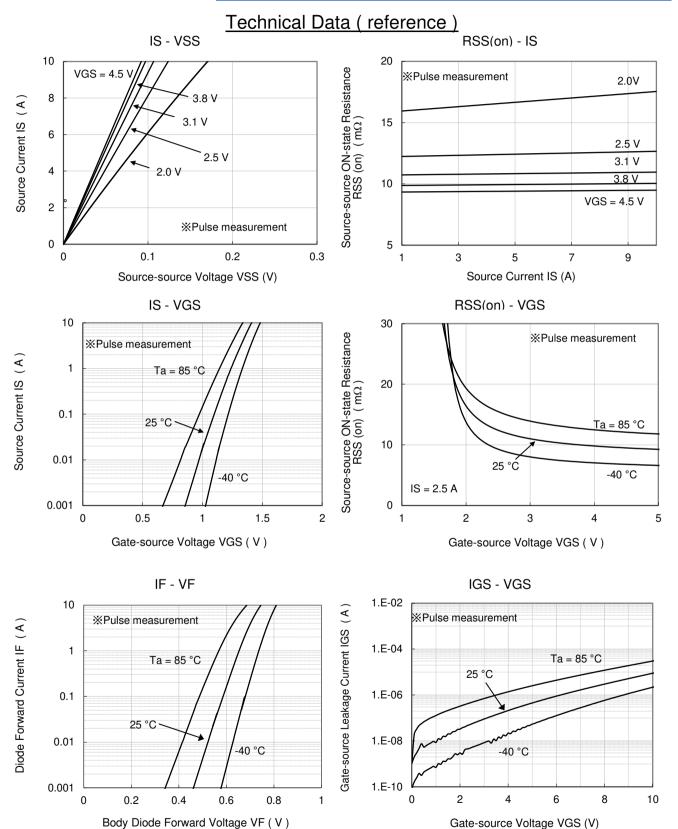


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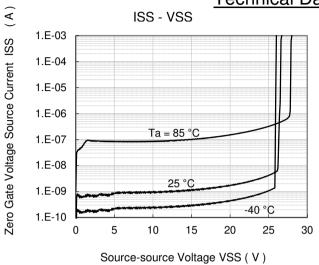


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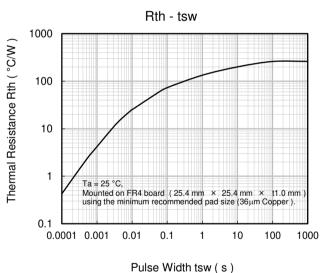
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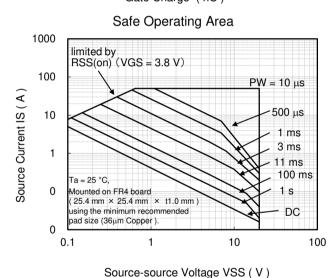
Panasonic

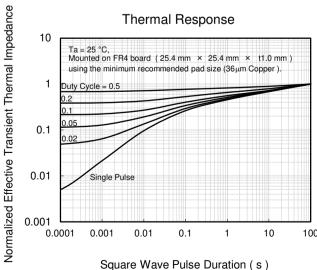




Dynamic Input/Output Characteristics 5.0 4.5 IS = 2.5 AGate - source Voltage VGS (V) 4.0 8 V 3.5 10 V 3.0 2.5 VDD = 12 V 2.0 1.5 1.0 0.5 0.0 5 10 25 30 15 20 Gate Charge (nC)







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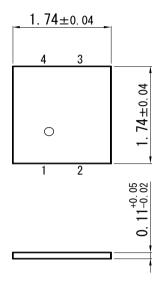
Panasonic

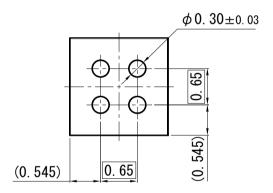
MOS FET

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■ Outline (MLGA004-W-1717-RB)

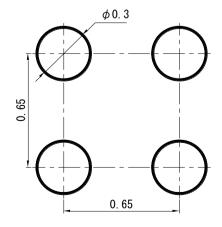
Unit: mm





■ Land Pattern (Reference)

Unit: mm



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